

EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	10313	((349/42,43,46) or (438/149,158)).OCLS.	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2010/08/28 15:42
L2	1413	(216/18).OCLS.	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2010/08/28 15:42
L3	26	L2 and (tft or tfts or (thin adj film adj (transistor or transistors)))	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2010/08/28 15:42
L4	5	L2 and L1	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2010/08/28 15:42
L5	10230	(tft or tfts or (thin adj film adj (transistor or transistors))) near5 (manufacturing or fabrication or formation or method or process).ti,ab.	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2010/08/28 15:42
L6	51177	gate adj2 (conductor or wire or wiring or metal or material)	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2010/08/28 15:42
L7	3481	L6 with (trench or groove or recess or depression)	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2010/08/28 15:42
L8	23	L5 and L7	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2010/08/28 15:42
L9	983	L7 with (insulation or insulating or insulator)	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2010/08/28 15:42
L10	48	L9 and (tft or tfts or (thin adj film adj (transistor or transistors)))	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2010/08/28 15:42

L11	85	L3 or L4 or L8 or L10	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2010/08/28 15:42
L12	3013	(semiconductor or semiconductive or semiconducting or silicon) near5 (etched or etching or patterned or patterning) near5 (concurrent or concurrently or simultaneous or simultaneously)	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2010/08/28 15:42
L13	177969	(conductor or conductive or wire or wiring or metal or material) near5 (trench or groove or recess or depression or bank)	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2010/08/28 15:42
L14	23587	L13 with (insulator or insulating or insulation)	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2010/08/28 15:42
L15	259	(L1 or L5) and L14	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2010/08/28 15:42
L16	23	L12 same L14	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2010/08/28 15:42
L17	354	L15 or L16 or L11	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2010/08/28 15:42
L18	21	17 and @pd>"20100206"	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2010/08/28 15:42
L20	52105	(tft or tfts or (thin adj film adj (transistor or transistors))).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2010/08/28 16:04
L21	284527	(spurt\$3 or inkjet\$4 or jet \$4 or droplet or droplets).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2010/08/28 16:05

L22	1145	20 and 21	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2010/08/28 16:05
L26	7844	(etch or etched or etching) near5 (ohmic or (contact adj (layer or film)))	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2010/08/28 16:07
L27	38	22 and 26	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2010/08/28 16:07
L28	4335	(buried or burying or embedded or embedding) near5 (gate adj electrode)	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2010/08/28 16:24
L29	86	20 and 28	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2010/08/28 16:24

EAST Search History (I nterference)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L36	2566	(conductor or conductive or wire or wiring or metal or material) near5 (trench or groove or recess or depression or bank) near5 (insulation or insulating).clm.	US-PGPUB; UPAD	OR	OFF	2010/08/28 17:01
L37	146533	(spurt\$3 or inkjet\$4 or jet\$4 or droplet or droplets or solution).clm.	US-PGPUB; UPAD	OR	OFF	2010/08/28 17:01
L38	179	36 and 37	US-PGPUB; UPAD	OR	OFF	2010/08/28 17:01
L40	6	38 and ((semiconductor or semiconductive or silicon or si) near10 etch \$3 near10 (mask or pattern)).clm.	US-PGPUB; UPAD	OR	OFF	2010/08/28 17:03
L41	0	38 and (ohmic near10 etch\$3).clm.	US-PGPUB; UPAD	OR	OFF	2010/08/28 17:07

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